

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	34	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	180	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	30			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	1.2		2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			...100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 10A		9.5	12	m
		V _{GS} = 4.5V, I _D = 8A		12	15	m
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 5A		6		S
Source-drain voltage	V _{SD}	I _S = 10A			1.28	V

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Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz	-	1200	-	pF
Output capacitance	C _{oss}		-	235	-	
Reverse transfer capacitance	C _{rss}		-	120	-	

Gate Charge characteristics(T_a = 25)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 25V	-	12	-	nC
Gate - Source charge	Q _{gs}	I _D = 8A	-	4	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	6	-	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20A, di/dt = 100A/μs		6.5		nS
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 20A, di/dt = 100A/μs		7		nC

